Ref #	Hits	Search Query	DBs	Default Operato r	Plural s	Time Stamp
L1	336	etch\$ with trench with horizontal with vertical	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/01/07 21:00
L2	256	1 and (insulat\$4 or oxide or ntiride) with trench	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/01/07 20:42
L3	1	1 and (insulat\$4 or oxide or ntiride) with trench with grid	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/01/07 20:42
L4	256	1 and (insulat\$4 or oxide or ntiride) with trench	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/01/07 20:42
L5	4	4 and ( second adj etch\$ with (oxide or nitride or insulat\$4) with trench)	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/01/07 20:44

L6	11860	grid with interconnect\$4	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/01/07 21:01
L7	170	6 and etch\$4 with trench	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/01/07 20:44
L8	102	7 and (trench with (insulat\$4 or oxide or nitride))	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/01/07 20:45
L9	35	7 and (trench with (insulat\$4 or oxide or nitride) same grid)	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/01/07 21:01
L10	34	9 and (etch\$4 with (insulat\$4 or oxide or nitride))	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/01/07 20:46

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L11	2	10 and second adj grid	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/01/07 20:46
L12	1546	438/151.ccls.	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/01/07 21:00
L13	2054	438/149.ccls.	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/01/07 21:00
L14	865	438/597.ccls.	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/01/07 21:00
L15	825	438/164.ccls.	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/01/07 21:00

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L16	2330	438/586.ccls.	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/01/07 21:00
L17	1183	438/672.ccls.	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/01/07 21:00
L18	2882	438/622.ccls.	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/01/07 21:00
L19	0	10 and etch\$ with trench with horizontal with vertical	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/01/07 21:00
L20	9	12 and grid with interconnect\$4	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/01/07 21:01

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L21	8	13 and grid with interconnect\$4	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/01/07 21:01
L22	13	14 and grid with interconnect\$4	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/01/07 21:01
L23	2	15 and grid with interconnect\$4	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/01/07 21:01
L24	3	16 and grid with interconnect\$4	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/01/07 21:01
L25	5	17 and grid with interconnect\$4	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/01/07 21:01

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L26	28	18 and grid with interconnect\$4	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/01/07 21:01
L27	4	20 and (trench with (insulat\$4 or oxide or nitride) same grid)	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/01/07 21:02
L28	3	21 and (trench with (insulat\$4 or oxide or nitride) same grid)	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/01/07 21:02
L29	2	22 and (trench with (insulat\$4 or oxide or nitride) same grid)	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/01/07 21:02
L30	1	23 and (trench with (insulat\$4 or oxide or nitride) same grid)	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/01/07 21:02

L31	2	24 and (trench with (insulat\$4 or oxide or nitride) same grid)	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/01/07 21:03
L32	2	25 and (trench with (insulat\$4 or oxide or nitride) same grid)	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/01/07 21:02
L33	1	26 and (trench with (insulat\$4 or oxide or nitride) same grid)	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/01/07 21:02